

Silicon PNP Power Transistor

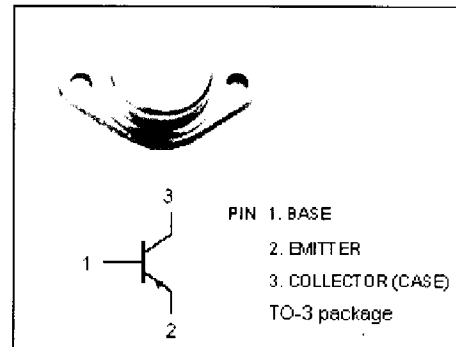
2SA1065

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min.})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SC2489

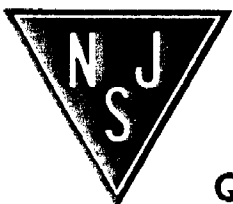
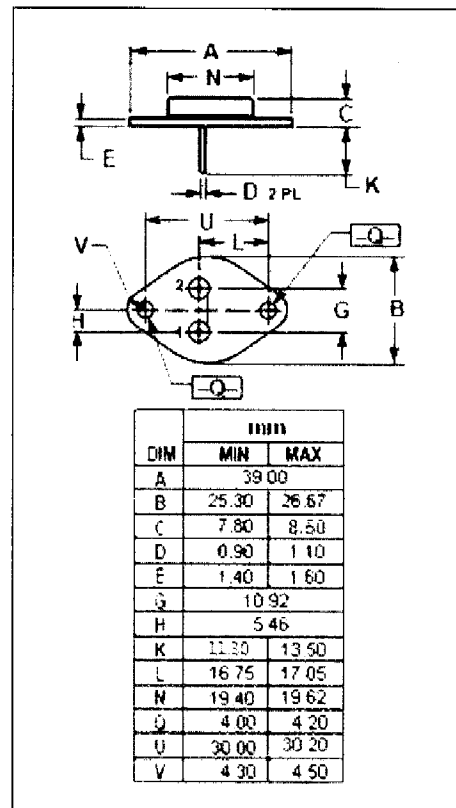
APPLICATIONS

- Designed for AF amplifier, high power amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	120	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -8A; I _B = -0.8A			-2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -10A; V _{CE} = -5V			-2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -70V; I _E = 0			-1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-2	mA
h _{FE-1}	DC Current Gain	I _C = -2A; V _{CE} = -5V	40		280	
h _{FE-2}	DC Current Gain	I _C = -10A; V _{CE} = -5V	30			
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -10V		50		MHz

◆ h_{FE-2} Classifications

R	Q	P	O
40-80	60-120	90-180	140-280